

8-9

Attorney's Docket No. 5308-168

**PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re: Das et al.  
Serial No.: 09/878,442  
Filed: June 11, 2001

Confirmation No.: 2584  
Group Art Unit: 2815  
Examiner: J. Jackson, Jr.

For: HIGH VOLTAGE, HIGH TEMPERATURE CAPACITOR STRUCTURES  
AND METHODS OF FABRICATING SAME

Date: July 16, 2003

Mail Stop Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**FAX RECEIVED**

JUL 16 2003

**INFORMATION DISCLOSURE STATEMENT TECHNOLOGY CENTER 2800  
PURSUANT TO 37 C.F.R. § 1.97(d)**

Sir:

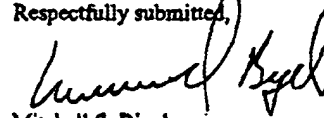
This is an Information Disclosure Statement in accordance with 37 C.F.R. § 1.97(d) and a petition for consideration of an Information Disclosure Statement in accordance with 37 C.F.R. § 1.97(d)(2). Please charge Deposit Account No. 50-0220 in the amount of \$180.00 for the petition fee set forth in 37 C.F.R. § 1.17(i) as required by 37 C.F.R. § 1.92(d)(3). The Commissioner is authorized to charge any additional fee, or credit any refund, to our Deposit Account No. 50-0220.

This Information Disclosure Statement is being filed after a Notice of Allowance under 37 C.F.R. § 1.311, but before payment of the Issue Fee. The Notice of Allowance was mailed on June 18, 2003.

Attached is a list of documents on form PTO-1449 together with copies of each identified document. In accordance with the requirements of 37 C.F.R. § 1.97(d)(1), the following Certification as specified in 37 C.F.R. § 1.97(e) is made. Each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application not more than three (3) months prior to the filing of this Information Disclosure Statement.

08/11/2003 TLBU11 00000007 500220 09878442  
01 FC:1806 180.00 BA

Respectfully submitted,



Mitchell S. Bigel  
Registration No. 29,614

**Match and Return**

<b>FORM PTO-1449 U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>					<b>Attorney Docket Number</b> 5308-168		<b>Serial No.</b> 09/878,442	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> (Use several sheets if necessary)								
<b>Applicants:</b> Das et al.								
<b>Filing Date:</b> June 11, 2001							<b>Group</b> 2815	
<b>U.S. PATENT DOCUMENTS</b>								
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate		
1	5,587,870	12/24/96	Anderson et al.	361	313			
<b>FOREIGN PATENT DOCUMENTS</b>								
Document Number	Date	Country	Class	Subclass	Translation Yes   No			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
2	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> , Vol. 47, No. 2, February 2000.							
3	Invitation to Pay Additional Fees for PCT/US02/09393 dated 7/1/03.							

FAX RECEIVED

JUL 16 2003

TECHNOLOGY CENTER 2800

EXAMINER  
\*EXAMINER

DATE CONSIDERED

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.